

**INTRODUCE:**

HVGT high voltage silicon rectifier diodes is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

**FEATURES:**

1. High reliability design.
2. High voltage, large current..
3. High frequency, Ultra Fast recovery.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

**APPLICATIONS:**

1. High voltage multiplier circuit
2. High frequency switching power supply .
3. General purpose high voltage rectifier.
4. Laser power supply medical equipment..

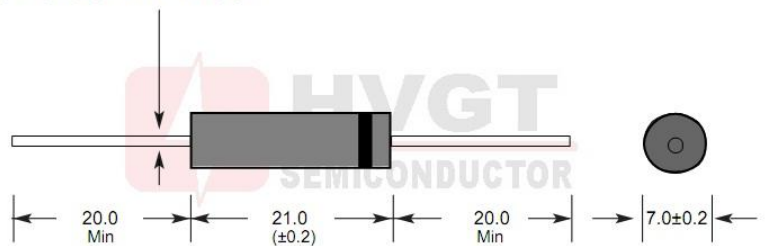
**MECHANICAL DATA:**

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 2.10 grams (approx).

**SHAPE DISPLAY:**

**SIZE: (Unit:mm)**
**HVGT NAME: DO-721**
**DO-721 Series**

Lead Diameter 1.2mm ±0.02



Unit:mm

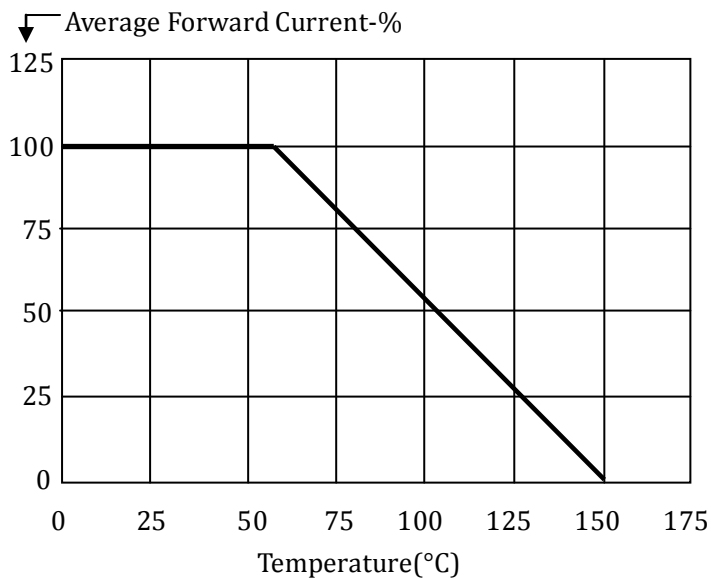
**MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)**

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_A=25^{\circ}C$	10	kV
Non-Repetitive Peak Reverse Voltage	$V_{RSM}$	$T_A=25^{\circ}C$	12	kV
Average Forward Current Maximum	$I_{FAVM}$	$T_A=55^{\circ}C$	500	mA
		$T_{OIL}=55^{\circ}C$	600	mA
Non-Repetitive Forward Surge Current	$I_{FSM}$	$T_A=25^{\circ}C$ ; 60Hz Half-Sine Wave; 8.3ms	20	A
Junction Temperature	$T_J$		150	$^{\circ}C$
Allowable Operation Case Temperature	$T_C$		-40~+150	$^{\circ}C$
Storage Temperature	$T_{STG}$		-40~+150	$^{\circ}C$

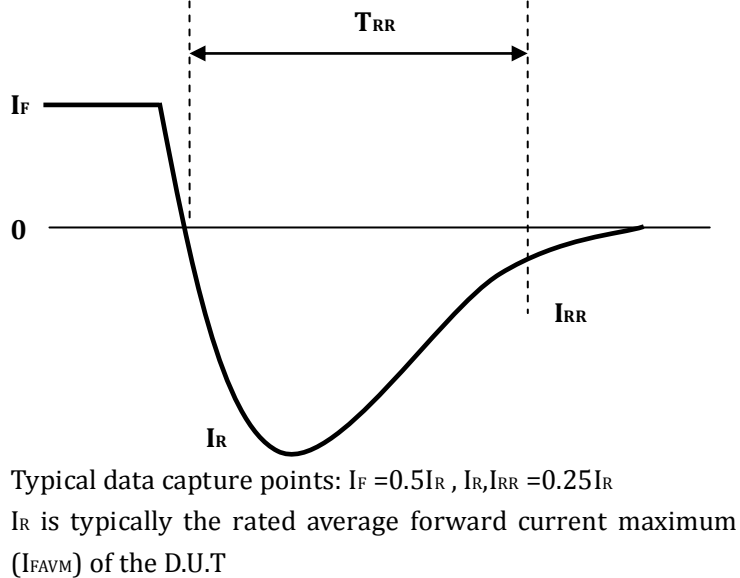
**ELECTRICAL CHARACTERISTICS:  $T_A=25^{\circ}C$  (Unless Otherwise Specified)**

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	$V_{FM}$	at $25^{\circ}C$ ; at $I_{FAVM}$	12	V
Maximum Reverse Current	$I_{R1}$	at $25^{\circ}C$ ; at $V_{RRM}$	0.5	$\mu A$
	$I_{R2}$	at $125^{\circ}C$ ; at $V_{RRM}$	50	$\mu A$
Maximum Reverse Recovery Time	$T_{RR}$	at $25^{\circ}C$ ; $I_F=0.5I_R$ ; $I_R=I_{FAVM}$ ; $I_{RR}=0.25I_R$	50	nS
Junction Capacitance	$C_J$	at $25^{\circ}C$ ; $V_R=0V$ ; $f=1MHz$	4.9	pF

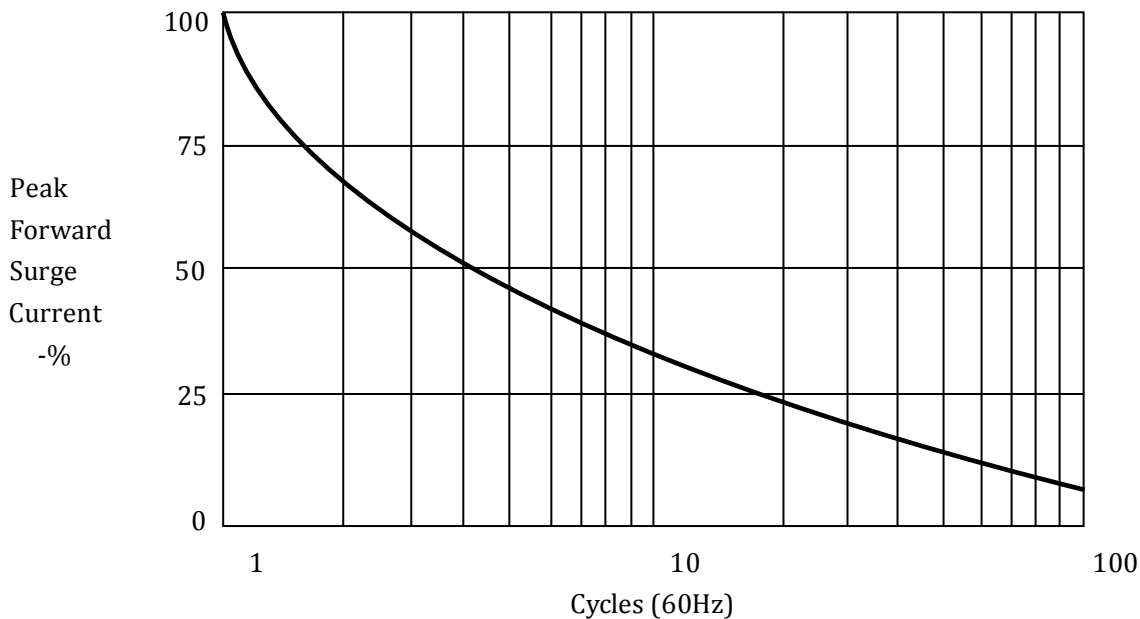
**Forward Current Derating Curve**



**Reverse Recovery Measurement Waveform**



**Non-Repetitive Surge Current**



**MARKING:**

Type	Code	Cathode Mark
GH05U10J	GH05U10J HVGT	

**PART NUMBER NOTE:**

Chip	Frequency	$I_{F(AV)}$	$T_{RR}$	$V_{RRM}$	Dimension Shape Code
<b>G</b>	<b>H</b>	<b>05</b>	<b>U</b>	<b>10</b>	<b>J</b>
GPP chip	High Frequency	0.5A	Ultra Fast Recovery	10kV	J=DO-721